IXYS

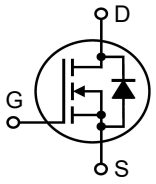
X2-Class Power MOSFET

IXTQ34N65X2M

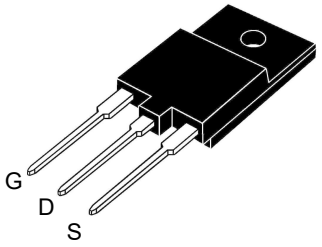
V_{DSS} = 650V
I_{D25} = 34A
$R_{DS(on)}$ ≤ 96mΩ

(Electrically Isolated Tab)

N-Channel Enhancement Mode
Avalanche Rated



OVERMOLDED (IXTQ...M) OUTLINE



G = Gate D = Drain
S = Source

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	650	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1 MΩ	650	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	T_C = 25°C, Limited by T_{JM}	34	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	48	A
I_A	T_C = 25°C	17	A
E_{AS}	T_C = 25°C	1	J
dv/dt	$I_S \le I_{DM}$, $V_{DD} \le V_{DSS}$, T_J =150°C	15	V/ns
P_D	T_C = 25°C	43	W
T_J		- 55 ... +150	°C
T_{JM}		150	°C
T_{stg}		- 55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering 1.6 mm (0.062 in.) from Case for 10s	300	°C
V_{ISOL}	50/60 Hz, 1 Minute	2500	V~
M_d	Mounting Torque	1.13/10	Nm/lb.in
Weight		5	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.
BV_{DSS}	V_{GS} = 0V, I_D = 1mA	650		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = 250μA	3.0		5.0 V
I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V			±100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			10 μA
	T_J = 125°C			150 μA
$R_{DS(on)}$	V_{GS} = 10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			96 mΩ

Features

- Plastic Overmolded Tab for Electrical Isolation
- Avalanche Rated
- 2500V~ Electrical Isolation
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Laser Drivers
- AC and DC Motor Drives
- Robotics and Servo Controls

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Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
g_{fs}	V_{DS} = 10V, I_D = 0.5 • I_{D25}, Note 1	20	30		S
R_{Gi}	Gate Input Resistance		0.90		Ω
C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		3000		pF
C_{oss}			2180		pF
C_{rss}			1.7		pF
	Effective Output Capacitance				
$C_{o(er)}$	Energy related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		125		pF
$C_{o(tr)}$	Time related; V_{GS} = 0V, V_{DS} = 0.8 • V_{DSS}		490		pF
$t_{d(on)}$	**Resistive Switching Times**		30		ns
t_r	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		48		ns
$t_{d(off)}$	R_G = 10Ω (External)		68		ns
t_f			30		ns
$Q_{g(on)}$	V_{GS} = 10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		54		nC
Q_{gs}			15		nC
Q_{gd}			20		nC
R_{thJC}				2.9	°C/W
R_{thCS}			0.25		°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max	
I_S	V_{GS} = 0V			34	A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			136	A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			1.4	V
t_{rr}	I_F = 17A, -di/dt = 100A/μs		390		ns
Q_{RM}	V_R = 100V		4.2		μC
I_{RM}			21.8		A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2 %.

Littelfuse reserves the Right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or moreof the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

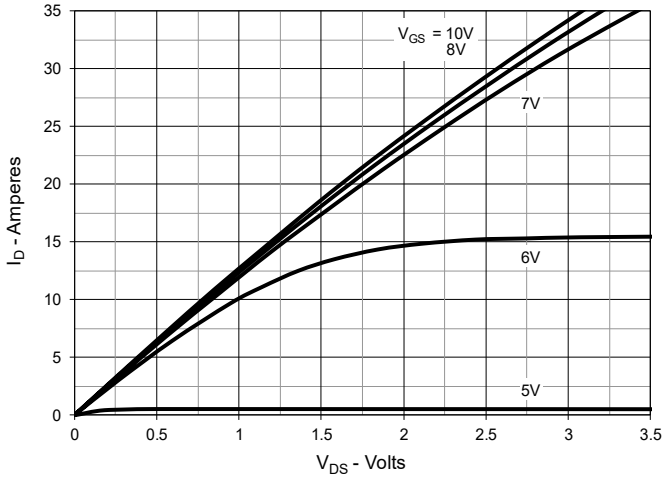

Fig. 2. Extended Output Characteristics @ T_J = 25ºC

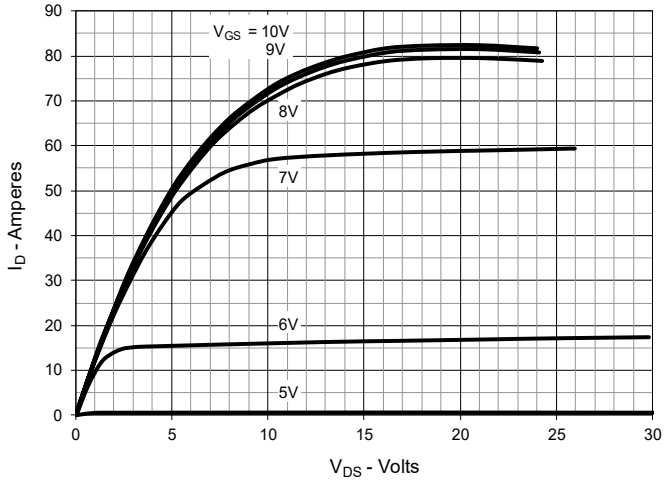

Fig. 3. Output Characteristics @ T_J = 125ºC

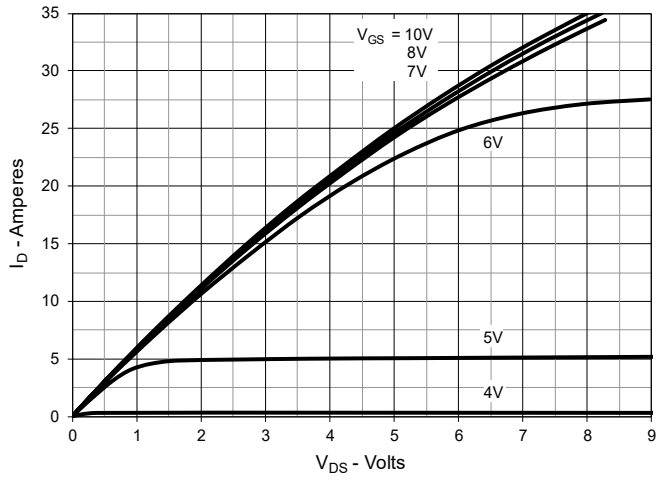

Fig. 4. $R_{DS(on)}$ Normalized to I_D = 17A Value vs. Junction Temperature

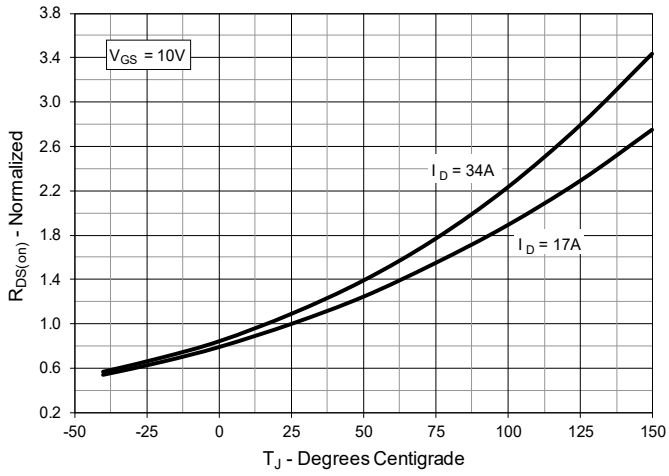

Fig. 5. $R_{DS(on)}$ Normalized to I_D = 17A Value vs. Drain Current

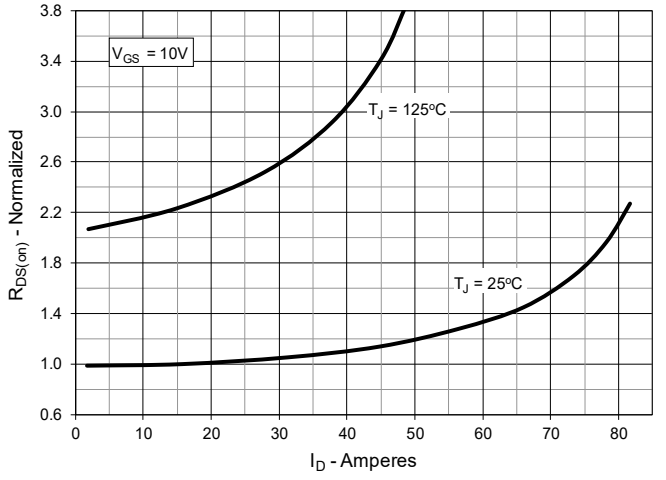

Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

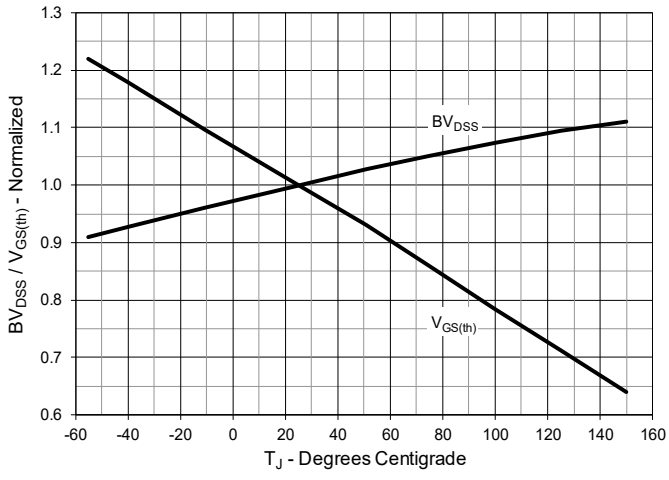

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Fig. 7. Input Admittance

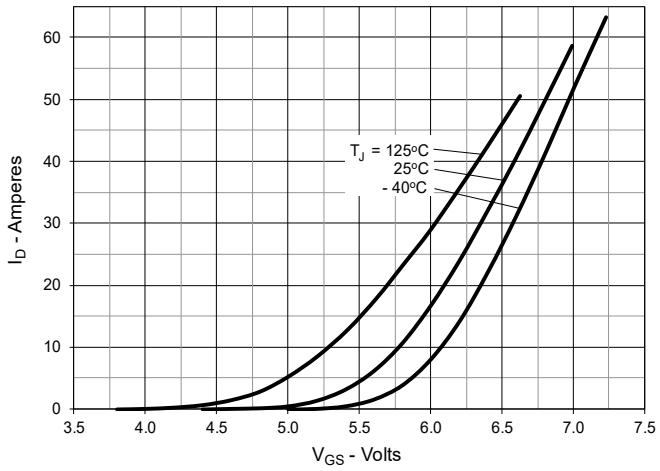

Fig. 8. Transconductance

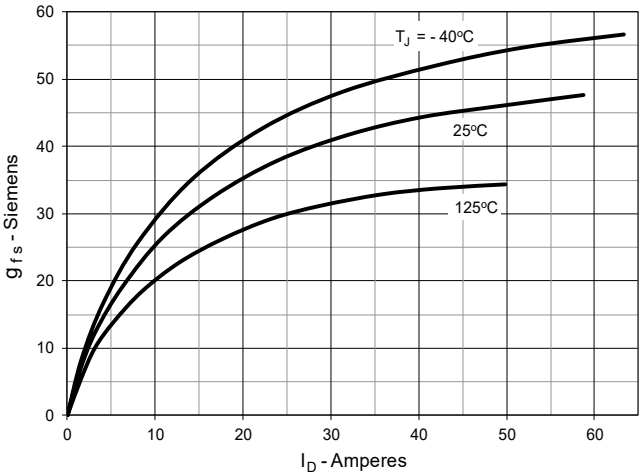

Fig. 9. Forward Voltage Drop of Intrinsic Diode

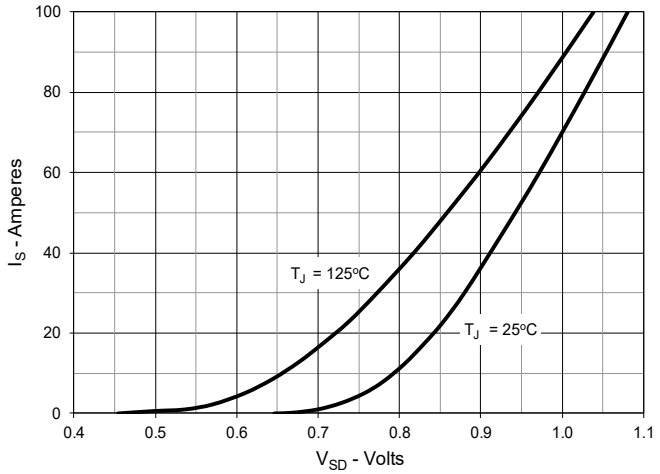

Fig. 10. Gate Charge

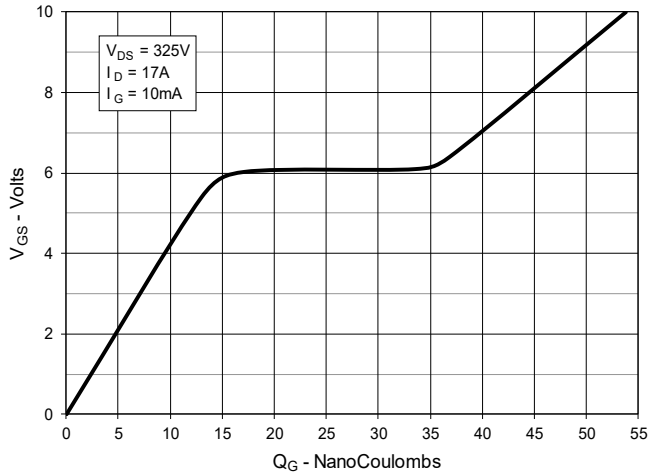

Fig. 11. Capacitance

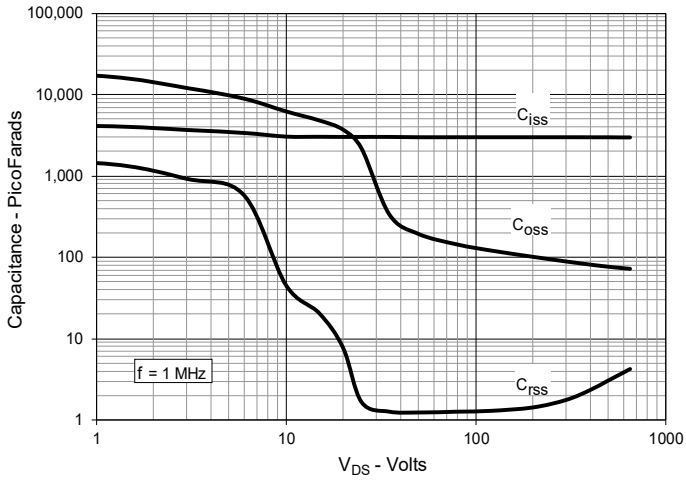

Fig. 12. Output Capacitance Stored Energy

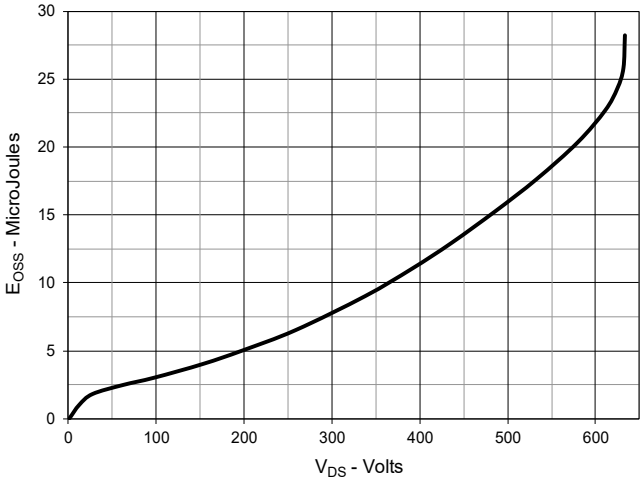

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Fig. 13. Forward-Bias Safe Operating Area

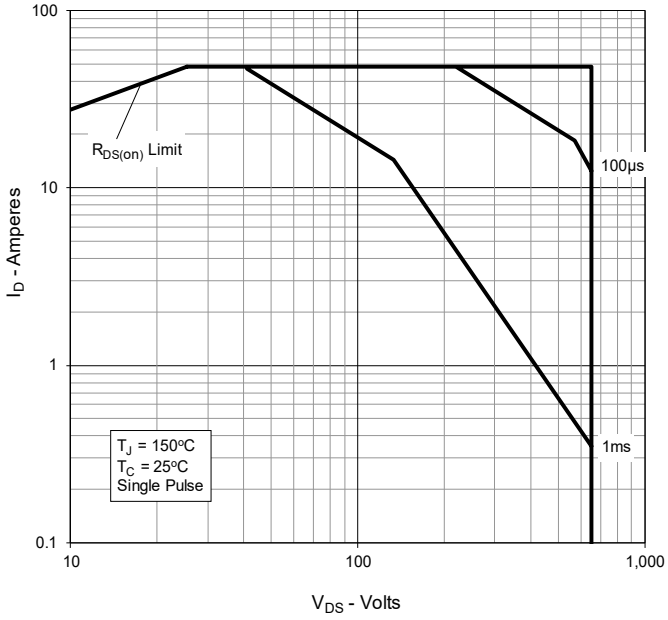
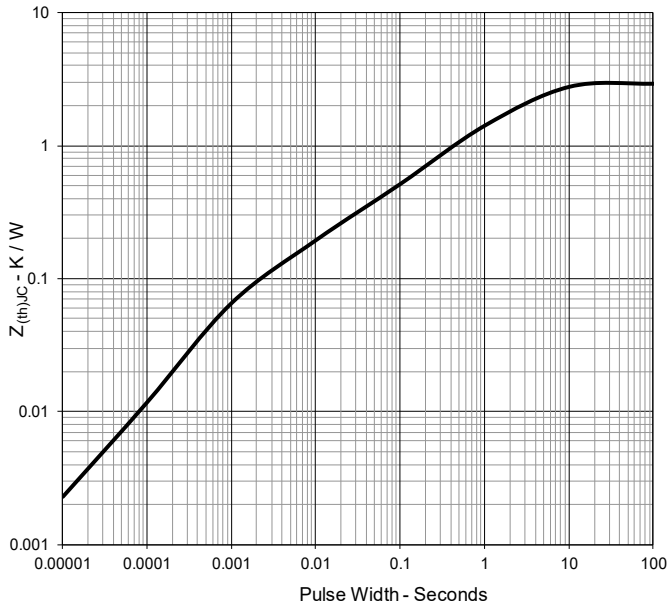


Fig. 14. Maximum Transient Thermal Impedance



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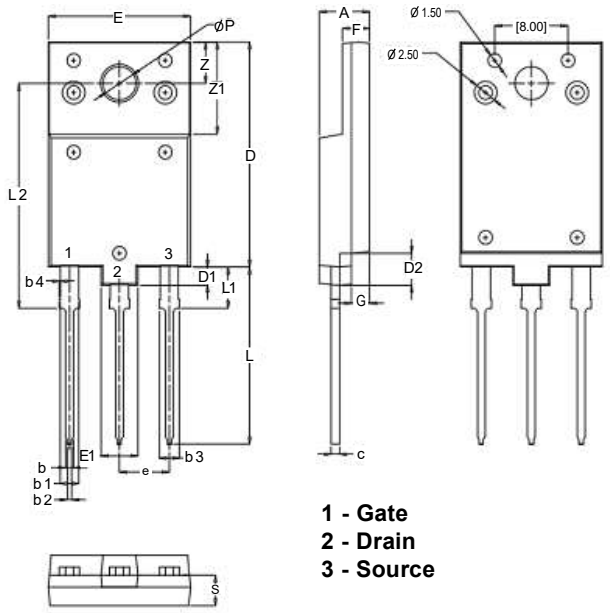
TO-3PFP Outline



1 - Gate
2 - Drain
3 - Source

SYMBOL	MIN	MAX
A	5.30	5.70
b	0.65	0.95
b1	1.81	2.19
b2	0.30	0.70
b3	1.81	2.40
b4	-	0.20
c	0.80	1.00
D	24.20	24.80
D1	1.80	2.20
D2	3.30	3.70
E	15.30	15.70
E1	3.80	4.20
F	2.80	3.20
e	5.45 BSC	
L	19.00	19.60
L1	4.20	4.80
L2	24.20	24.80
P	3.40	3.80
Z	4.30	4.70
Z1	9.70	10.30
G	1.80	2.20
S	3.10	3.50

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